



an Open Access Journal by MDPI

Nanowire Field-Effect Transistor (FET)

Guest Editors:

Prof. Antonio García-Loureiro

CITIUS, Universidade de Santiago de Compostela, 15782 Santiago de Compostela, Galicia, Spain

Prof. Karol Kalna

Nanoelectronic Devices
Computational Group, College of Engineering, Bay Campus
Swansea University, Fabian Way,
Crymlyn Burrows SA1 8EN, UK

Dr. Natalia Seoane

CITIUS, Universidade de Santiago de Compostela, 15782 Santiago de Compostela, Galicia, Spain

Deadline for manuscript
submissions:

closed (29 February 2020)

Message from the Guest Editors

In the last few years, the main semiconductor industries have introduced multi-gate non-planar transistors in their core business with applications to memories and logical integrated circuits in order to achieve a larger integration on chip, increase performance, and reduce energy consumption. There is intense research underway to keep developing these devices and address their limitations in order to continue transistor scaling while further improving performance.

Nanowire Field-Effect Transistors (NW-FETs) are nowadays one of the strongest contenders to replace Fin Field-Effect Transistors (FinFETs) in the following technological nodes, because of their superior electrostatic control of the channel transport via a gate-all-around gate.

This Special Issue represents a good opportunity for researchers around the world to disseminate their recent progress related to NW-FETs, from three different points of view: Physics, technology and modelling. Therefore, of particular interest for this Special Issue are material properties, fabrication, design optimization, characterization, numerical and analytical modelling, and variability and circuit design.



mdpi.com/si/17060

Special Issue



an Open Access Journal by MDPI

Editor-in-Chief

Prof. Dr. Maryam Tabrizian

1. Department of Biomedical Engineering, Faculty of Medicine and Health Sciences, McGill University, Montreal, QC H3A 2B6, Canada

2. Faculty of Dentistry and Oral Health Sciences, McGill University, 3640 Rue University, Montreal, QC H3A 0C7, Canada

Message from the Editor-in-Chief

Materials (ISSN 1996-1944) was launched in 2008. The journal covers twenty-five comprehensive topics: biomaterials, energy materials, advanced composites, advanced materials characterization, porous materials, manufacturing processes and systems, advanced nanomaterials and nanotechnology, smart materials, thin films and interfaces, catalytic materials, carbon materials, materials chemistry, materials physics, optics and photonics, corrosion, construction and building materials, materials simulation and design, electronic materials, advanced and functional ceramics and glasses, metals and alloys, soft matter, polymeric materials, quantum materials, mechanics of materials, green materials, general. *Materials* provides a unique opportunity to contribute high quality articles and to take advantage of its large readership.

Author Benefits

Open Access: free for readers, with article processing charges (APC) paid by authors or their institutions.

High Visibility: indexed within Scopus, SCIE (Web of Science), PubMed, PMC, Ei Compendex, CaPlus / SciFinder, Inspec, Astrophysics Data System, and other databases.

Journal Rank: JCR - Q1 (Metallurgy and Metallurgical Engineering) / CiteScore - Q2 (*Condensed Matter Physics*)

Contact Us

Materials Editorial Office
MDPI, Grosspeteranlage 5
4052 Basel, Switzerland

Tel: +41 61 683 77 34
www.mdpi.com

mdpi.com/journal/materials
materials@mdpi.com
[X@Materials_Mdpi](https://twitter.com/Materials_Mdpi)